

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

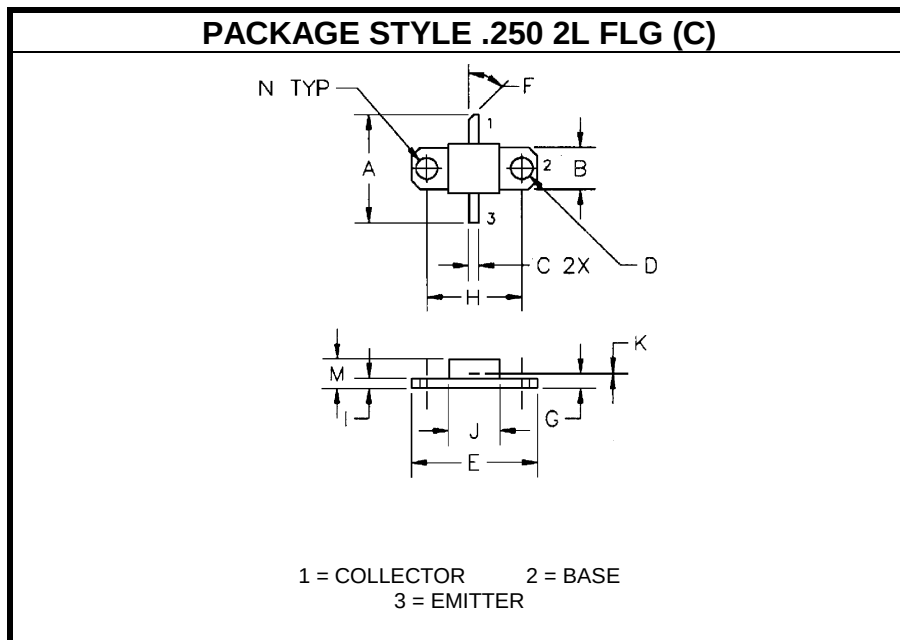
The **MRAL2023-3** is a Common Base Device Designed for class C Amplifier Applications in L-Band FM Microwave Links.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	0.5 A
V_{CES}	40 V
P_{DISS}	10 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	16 °C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 20 mA	40			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CBO}	V _{CB} = 22 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	10			---
C_{OB}	V _{CB} = 22 V f = 1.0 MHz			5	pF
P_G	V _{CE} = 22 V P _{OUT} = 3.0 W f = 2000 to 2300 MHz	8.0	8.5		dB
η_c			45		%